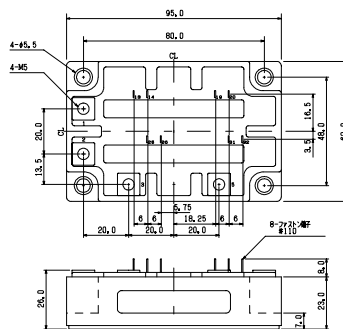
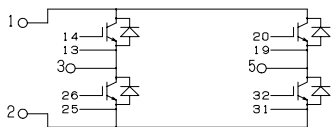


回路図 : CIRCUIT
外形寸法図 : OUTLINE DRAWING


8-faston tab # 110

Dimension: [mm]

最大定格 : MAXIMUM RATINGS (T_c=25)

重量 : 450 g

Item	Symbol	Rated Value	Unit
コレクタ・エミッタ間電圧 Collector-Emmitter Voltage	V _{CEs}	600	V
ゲート・エミッタ間電圧 Gate-Emmitter Voltage	V _{GES}	±20	V
コレクタ電流 Collector Current	DC	I _C = 150	A
	1ms	I _{CP} = 300	
コレクタ損失 Collector Power Dissipation	P _c	560	W
接合温度 Junction Temperature Range	T _j	-40 ~ +150	
保存温度 Storage Temperature Range	T _{stg}	-40 ~ +125	
絶縁耐圧 (Terminal to Base AC, 1 minute) Isolation Voltage	V _{ISO}	2500	V _(RMS)
締め付けトルク Mounting Torque	F _{tor}	2 (20.4)	N・m (kgf・cm)

電気的特性 : ELECTRICAL CHARACTERISTICS (T_c=25)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
コレクタ遮断電流 Collector-Emmitter Cut-Off Current	I _{CEs}	V _{CE} =600V, V _{GE} =0V	-	-	2.0	mA
ゲート漏れ電流 Gate-Emmitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} =0V	-	-	1.0	μA
コレクタ・エミッタ間飽和電圧 Collector-Emmitter Saturation Voltage	V _{CE(sat)}	I _C =150A, V _{GE} =15V	-	2.1	2.6	V
ゲートしきい値電圧 Gate-Emmitter Threshold Voltage	V _{GE(th)}	V _{CE} =5V, I _C =150mA	4.0	-	8.0	V
入力容量 Input Capacitance	C _{ies}	V _{CE} =10V, V _{GE} =0V, f=1MHz	-	15000	-	pF
スイッチング時間 Switching Time	上昇時間 Rise Time	V _{CE} =300V R _L =2 R _G =5.1 V _{GE} =±15V	-	0.15	0.3	μs
	ターンオン時間 Turn-on Time		-	0.25	0.4	
	下降時間 Fall Time		-	0.2	0.35	
	ターンオフ時間 Turn-off Time		-	0.45	0.7	

フリーホイールダイオードの特性 : FREE WHEELING DIODE RATINGS & CHARACTERISTICS (T_c=25)

Item	Symbol	Rated Value	Unit
順電流 Forward Current	DC	I _F = 150	A
	1ms	I _{FM} = 300	

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
順電圧 Peak Forward Voltage	V _F	I _F =150A, V _{GE} =0V	-	1.9	2.4	V
逆回復時間 Reverse Recovery Time	t _{rr}	I _F =150A, V _{GE} =-10V di/dt=150A/μs	-	0.15	0.25	μs

熱的特性 : THERMAL CHARACTERISTICS

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
熱抵抗 Thermal Impedance	IGBT	Junction to Case	-	-	0.22	/W
	Diode		-	-	0.45	

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Fig.1- Output Characteristics (Typical)

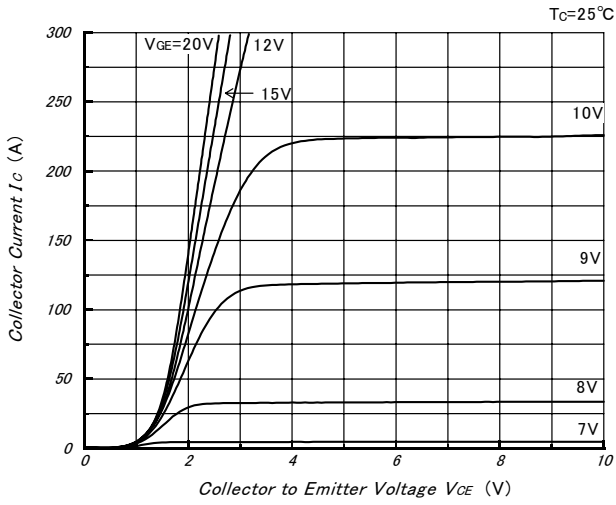


Fig.2- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

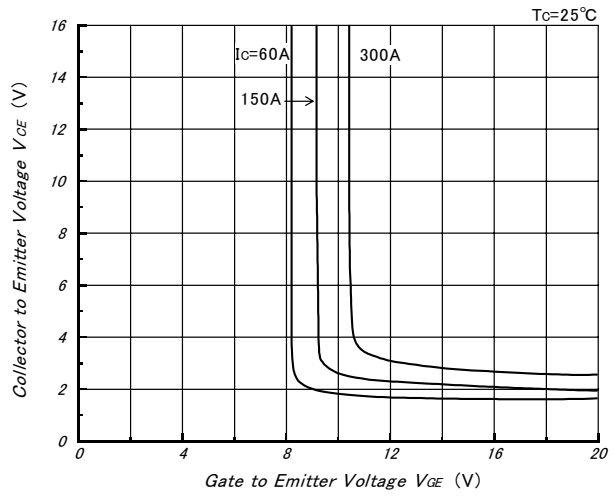


Fig.3- Collector to Emitter On Voltage vs. Gate to Emitter Voltage (Typical)

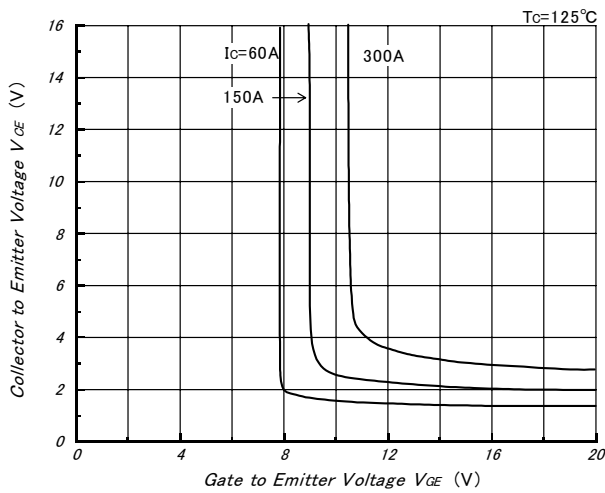


Fig.4- Gate Charge vs. Collector to Emitter Voltage (Typical)

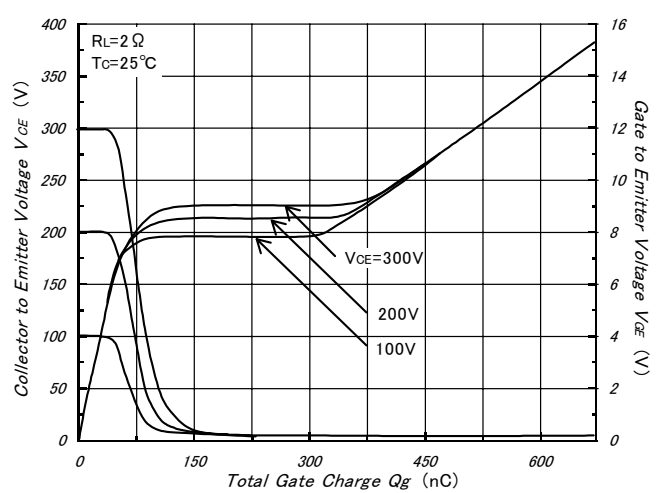


Fig.5- Capacitance vs. Collector to Emitter Voltage (Typical)

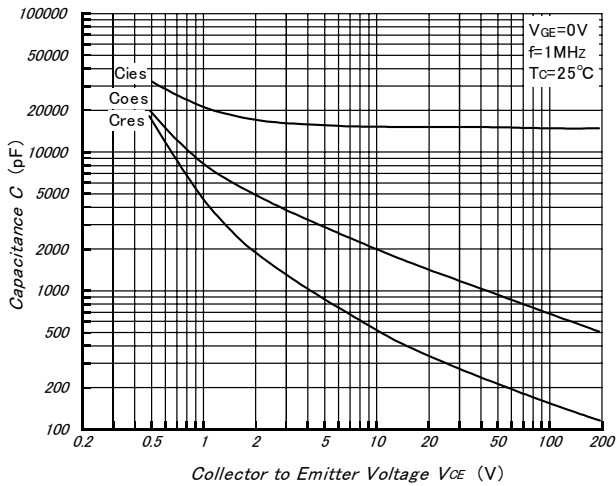
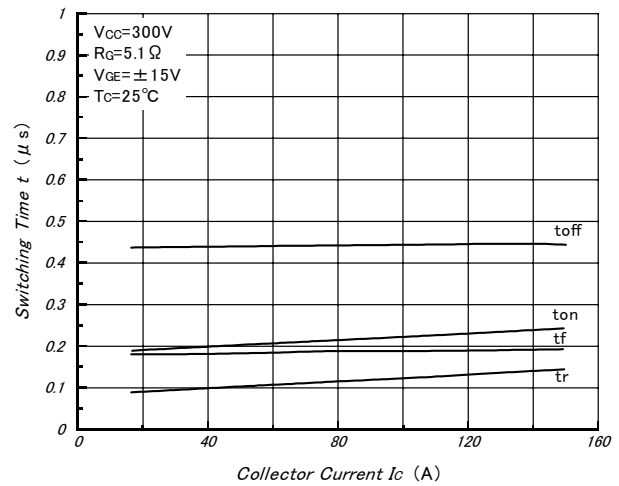


Fig.6- Collector Current vs. Switching Time (Typical)



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Fig.7- Series Gate Impedance vs. Switching Time (Typical)

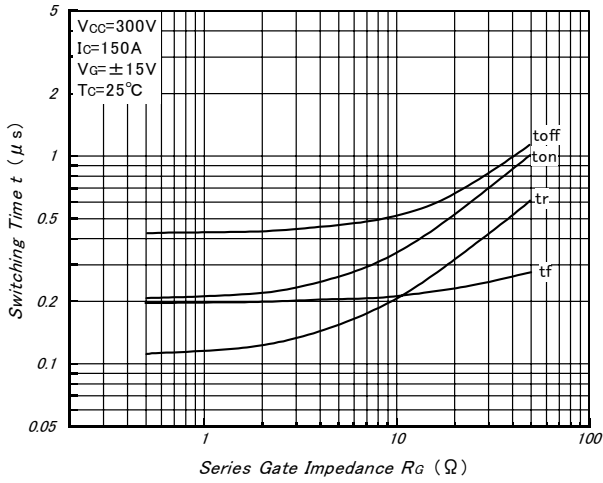


Fig.8- Forward Characteristics of Free Wheeling Diode (Typical)

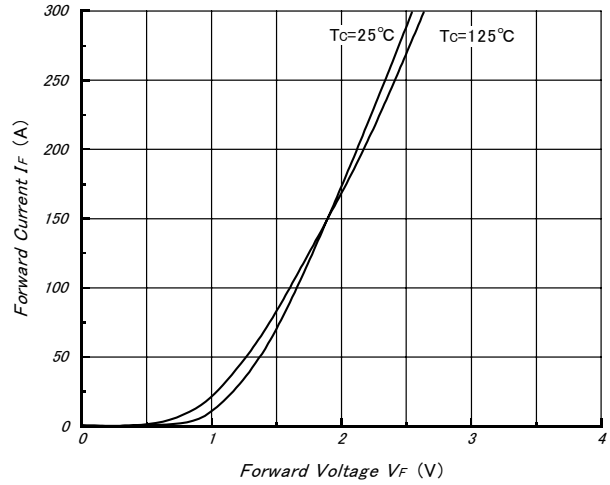


Fig.9- Reverse Recovery Characteristics (Typical)

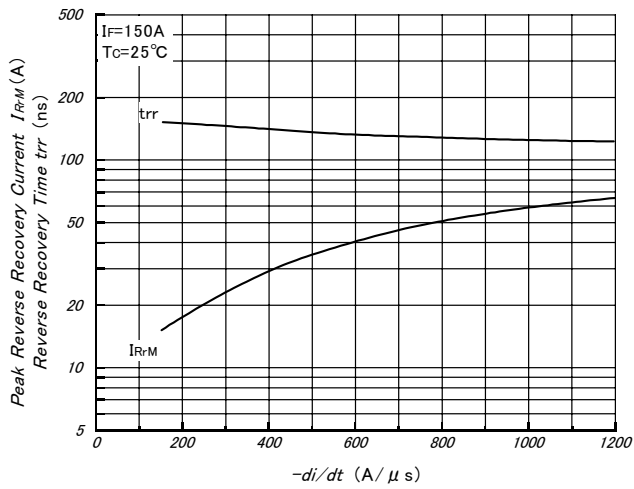


Fig.10- Reverse Bias Safe Operating Area (Typical)

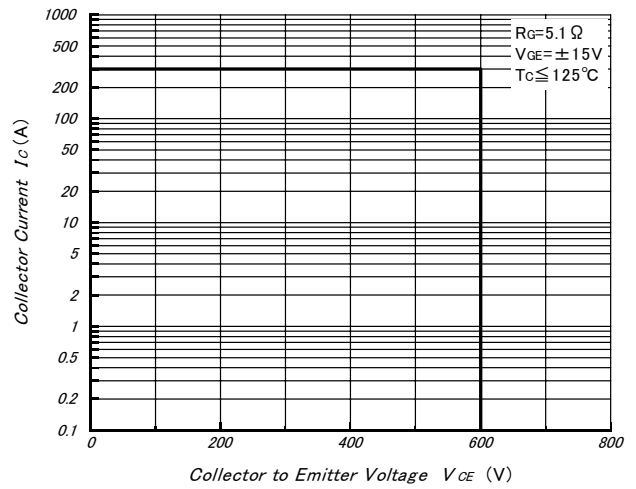


Fig.11- Transient Thermal Impedance

